



Patent Application No. 10/657,505
Customer Number: 42717

IPW

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Chii-Ming Wu

§ Docket No.: 24061.406
§ (TSMC2001-1247)

Serial No.: 10/657,505

§ Examiner: Kennedy, Jennifer M.

Filing Date: September 8, 2003

§ Art Unit: 2812

For: METHOD OF MANUFACTURING A CONTACT
INTERCONNECTION LAYER CONTAINING
A METAL AND NITROGEN BY ATOMIC
LAYER DEPOSITION FOR DEEP SUB-MICRON
SEMICONDUCTOR TECHNOLOGY

RESPONSE TO RESTRICTION REQUIREMENT

Mail Stop: Amendment
Commissioner for Patents
PO Box 1450
Alexandria, VA 22313-1450

Dear Sir:

In response to the second Office Action mailed June 30, 2005, Applicant thanks the Examiner for the additional time for reply and has identified the claims as required below:

Claims 1-25 as readable on Figs. 2a-2c and Fig. 3.

Claims 1-3, 5-16, and 18-25 as readable on Group A-1 ($Ti(OCH(CH_3)_2)_4$).

Claims 1-25 as readable on Group C-1 (MN).

Claims 1-24 as readable on Group D-1 (CMP).

Applicant withdraws the selection of Group B-1 (Silicon gas source) as this group contains limitations that do not exist in the selected embodiment.

An early action on the merits is respectfully requested.

Respectfully submitted,

Timothy F. Bliss

Timothy F. Bliss
Reg. No. 50,925

Date: 7/19/05

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CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Mail Stop: Amendment, Commissioner For Patents, PO Box 1450, Alexandria, VA 22313-1450 on the date below.

Name

Date

<i>Dayle Conner</i>	
7-22-05	
Date	